

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 64-024232

(43)Date of publication of application : 26.01.1989

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(51)Int.Cl. G02F 1/133

G09F 9/30

H01L 27/12

H01L 29/78

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(21)Application number : 62-181922 (71)Applicant : FUJITSU LTD

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(54) THIN FILM TRANSISTOR MATRIX

(57)Abstract:

PURPOSE: To suppress the fluctuation in the voltage of picture element electrodes by capacity coupling so that a sharp image is obtd. by forming an opaque conductive film coated on a drain bus line, gate bus line and thin film transistor via a protective insulating film.

CONSTITUTION: The opaque conductive film 7 is formed via the protective insulating film 6 on the drain bus line 2, gate bus line 3 and thin film transistor (TFT) 4 formed on an insulating substrate such as glass substrate 1. Namely, the potential conductive film 7 acts as a shielding film between the picture element electrode 5 and the drain bus line 2 if the conductive film 7 is connected to a ground end. The capacity component is then eliminated from the parasitic capacity and only the capacity component CD32 between the rear faces is eventually made to remain. The influence of the potential of the drain bus line 2 on the potential of the picture element electrode 5 is, thereby, extremely

minimized. The undesirable fluctuation in the voltages is thereby suppressed and the good image quality is obtd.

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LEGAL STATUS [Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]